

CLAIMS

What is claimed is:

1. A method for exposing a blanket photoresist layer comprising:
 providing a substrate having formed thereover a photoresist layer; and
 exposing within a single die region within the photoresist layer a minimum of two non-overlapping die sub-patterns while employing a minimum of two masks.
2. The method of claim 1 wherein the substrate is a semiconductor substrate.
3. The method of claim 1 wherein the substrate is a ceramic substrate.
4. The method of claim 1 wherein the blanket photoresist layer is formed of a positive photoresist material.
5. The method of claim 1 wherein the blanket photoresist layer is formed of a negative photoresist material.

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6. A method for exposing a photoresist layer comprising:
 providing a substrate having formed thereover a photoresist layer; and
 exposing within a single die region within the photoresist layer a minimum of two non-overlapping die sub-patterns while employing a minimum of two masks and two exposure conditions.
7. The method of claim 6 wherein the substrate is a semiconductor substrate.
8. The method of claim 6 wherein the substrate is a ceramic substrate.
9. The method of claim 6 wherein the photoresist layer is formed of a positive photoresist material.
10. The method of claim 6 wherein the photoresist layer is formed of a negative photoresist material.
11. The method of claim 6 wherein the exposure conditions include exposure energy.
12. The method of claim 6 wherein the exposure conditions include depth of focus.
13. The method of claim 6 wherein the exposure conditions include illumination.

14. A method for forming a patterned layer comprising:

providing a substrate having formed thereover a target layer having formed thereover a photoresist layer;

exposing within a single die region within the photoresist layer a minimum of two non-overlapping die sub-patterns while employing a minimum of two masks, to form an exposed photoresist layer;

developing the exposed photoresist layer to form a patterned photoresist layer; and

processing the target layer to form a processed target layer while employing the patterned photoresist layer as a mask layer.

15. The method of claim 1 wherein the substrate is a semiconductor substrate.

16. The method of claim 1 wherein the substrate is a ceramic substrate.

17. The method of claim 1 wherein the blanket photoresist layer is formed of a positive photoresist material.

18. The method of claim 1 wherein the blanket photoresist layer is formed of a negative photoresist material.

19. The method of claim 1 wherein the exposing of the photoresist layer employing two masks also employs at least two separate exposure conditions.

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20. The method of claim 19 wherein the separate exposure conditions are selected from the group including exposure energy, depth of focus and illumination.